



#### 40V N-CHANNEL ENHANCEMENT MODE MOSFET POWERDI®

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25 ℃		
40V	$12m\Omega$ @ $V_{GS} = 10V$	11.5A		
40 V	$15m\Omega @ V_{GS} = 4.5V$	10.3A		

#### **Features and Benefits**

- Low R<sub>DS(ON)</sub> ensures on state losses are minimized
- Small, form factor, thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Description and Applications**

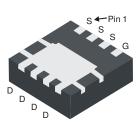
This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high-efficiency power management applications such as:

- Backlighting
- Power Management Functions
- DC-DC Converters

### **Mechanical Data**

- Case: POWERDI 3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208@3
- Weight: 0.072 grams (Approximate)

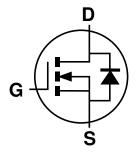
#### **POWERDI 3333-8**







Top View



Equivalent Circuit

### Ordering Information (Note 4)

Part Number	Case	Packaging
DMN4010LFG-7	POWERDI 3333-8	2,000/Tape & Reel
DMN4010LFG-13	POWERDI 3333-8	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

# **Marking Information**

**POWERDI 3333-8** 



N41= Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 13 = 2013) WW = Week Code (01 ~ 53)



## **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	40	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note C) V 10V	Steady State	T <sub>A</sub> = +25 °C T <sub>A</sub> = +70 °C	ID	11.5 9.2	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t<10s	T <sub>A</sub> = +25 °C T <sub>A</sub> = +70 °C	ID	14.2 11.4	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	80	Α		
Maximum Continuous Body Diode Forward Current (	Is	2	Α		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	27	Α		
Avalanche Energy (Note 7) L = 0.1mH	Eas	37	mJ		

# Thermal Characteristics (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 5)	$P_{D}$	0.93	W	
Thermal Begintenes, Junction to Ambient (Note 5)	Steady state	Б	137	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	89	
Total Power Dissipation (Note 6)		P <sub>D</sub>	2.45	W
Thermal Begintenes, Junction to Ambient (Note 6)	Steady state	Б	52	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	34	
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	3		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	∞

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

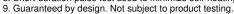
<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. 7.  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J = +25$  °C.

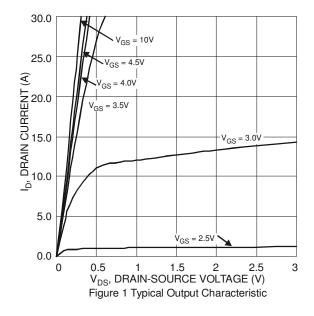


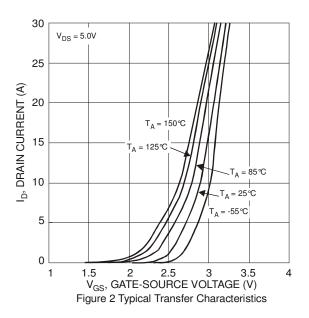
## Electrical Characteristics (@T<sub>A</sub> = +25 °C, unless otherwise specified.)

Characteristic		Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.0	_	3.0	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Chatia Duain Cauraa On Basistanaa	J	_	_	12	0	$V_{GS} = 10V, I_D = 14A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>		_	15	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 11A	
Diode Forward Voltage	$V_{SD}$	_	0.72	_	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 14A	
DYNAMIC CHARACTERISTICS (Note 9)			•	•			
Input Capacitance	C <sub>iss</sub>	_	1,810	_	pF	.,	
Output Capacitance	Coss	_	135	_	pF	$V_{DS} = 20V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	112	_	pF	-1 - 1.0Wii 12	
Gate Resistance	Rg	_	1.7	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	17	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	37	_	nC	), ooy   444	
Gate-Source Charge	Q <sub>gs</sub>	_	5.6	_	nC	$V_{DS} = 20V, I_D = 14A$	
Gate-Drain Charge	$Q_{gd}$	_	7.1	_	nC	1	
Turn-On Delay Time	t <sub>D(on)</sub>	_	5.1	_	ns		
Turn-On Rise Time	t <sub>r</sub>	_	13	_	ns	$V_{GS} = 10V, V_{DS} = 20V,$	
Turn-Off Delay Time	t <sub>D(off)</sub>	_	36	_	ns	$R_G = 6\Omega$ , $I_D = 14A$	
Turn-Off Fall Time	t <sub>f</sub>		13	_	ns	1	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	_	12.2	_	nS	$I_F = 3A$ , $di/dt = 100A/\mu s$	
Body Diode Reverse Recovery Charge		_	5.4		nC	$I_F = 3A$ , $di/dt = 100A/\mu s$	

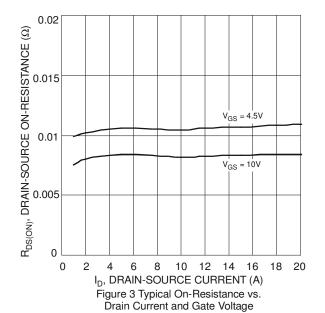
Notes: 8. Short duration pulse test used to minimize self-heating effect.

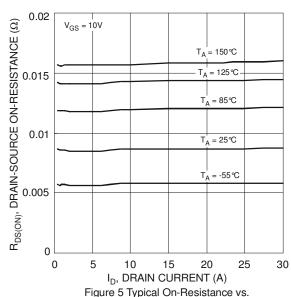












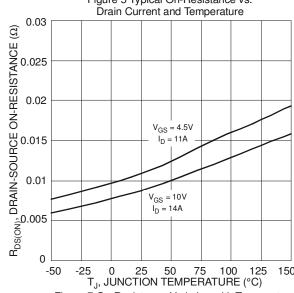
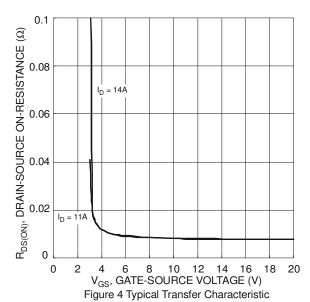


Figure 7 On-Resistance Variation with Temperature



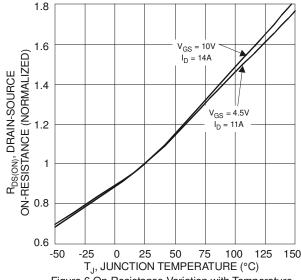


Figure 6 On-Resistance Variation with Temperature

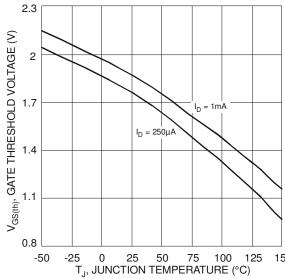
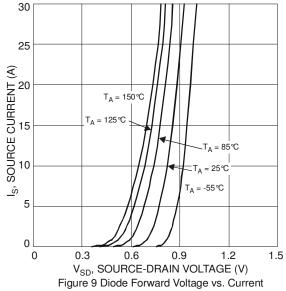
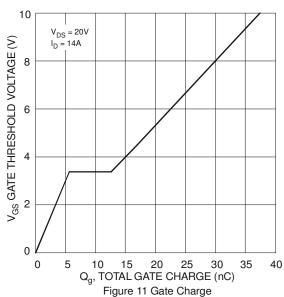
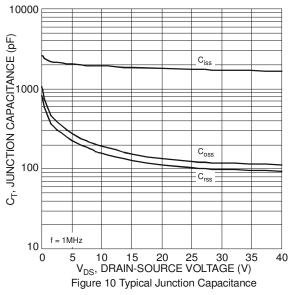


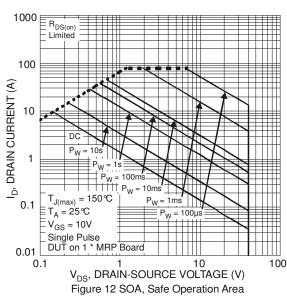
Figure 8 Gate Threshold Variation vs. Ambient Temperature

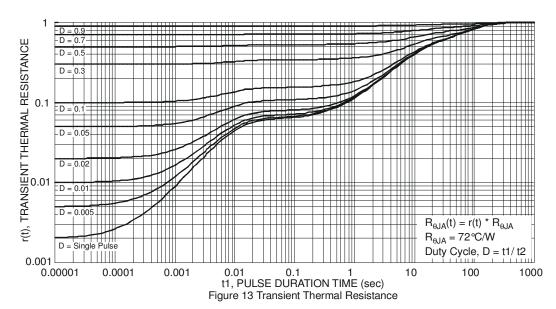








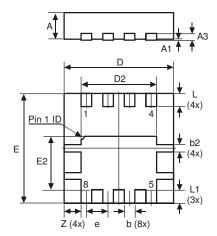






## **Package Outline Dimensions**

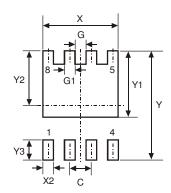
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



POWERDI®3333-8					
Dim	Min	Max	Тур		
D	3.25	3.35	3.30		
Е	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E2	1.56	1.66	1.61		
Α	0.75	0.85	0.80		
A1	0	0.05	0.02		
А3	_	_	0.203		
b	0.27	0.37	0.32		
b2	1	-	0.20		
L	0.35	0.45	0.40		
L1	_	_	0.39		
е	_	_	0.65		
Z	_	_	0.515		
All I	All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)			
C	0.650			
G	0.230			
G1	0.420			
Υ	3.700			
Y1	2.250			
Y2	1.850			
Y3	0.700			
Х	2.370			
X2	0.420			



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